

## Amendments to the Claims

1-14.(cancelled)

15.(new) An assembly for use in a semiconductor processing device configured to receive a gas injector, the assembly comprising:

a chamber configured to replace the gas injector in the device, the chamber open at one end and the chamber defining an inlet; and  
a seal disposed about the open end of the chamber.

16.(new) The assembly of Claim 15, wherein the chamber further defines an outlet.

17.(new) The assembly of Claim 16, further comprising a window in the chamber.

18.(new) An assembly for use in a semiconductor processing device configured to receive a gas injector, the assembly comprising:

a chamber configured to replace the gas injector in the device, the chamber open at one end and the chamber defining a liquid etchant inlet;  
a reservoir coupled to the inlet;  
a valve interposed between the reservoir and the inlet, the valve operative between an open position in which liquid etchant may flow from the reservoir to the inlet and a closed position in which liquid etchant may not flow from the reservoir to the inlet;  
and  
a seal disposed about the open end of the chamber.

19.(new) The assembly of Claim 18, wherein the chamber further defines a vapor outlet.

20.(new) The assembly of Claim 18, further comprising a window in the chamber.

- 21.(new) An etch injector, comprising:  
a box-shaped chamber open at one end, the chamber including opposing sidewalls, opposing endwalls and a cover plate attached to the sidewalls and endwalls, the cover plate defining an inlet port and an exhaust port; and  
a seal disposed along bottom surfaces of the sidewalls and the endwalls.
- 22.(new) The injector of Claim 21, wherein the inlet port comprises a liquid etchant inlet port and the exhaust port comprises an etchant vapor exhaust port.
- 23.(new) The injector of Claim 21, wherein the chamber is sized and shaped to replace a gas injector in a muffle during maintenance operations for removing residue from a lower surface of the muffle.
- 24.(new) The injector of Claim 21, wherein the seal comprises an O ring disposed in a recess along the bottom surfaces of the sidewalls and the endwalls.
- 25.(new) The injector of Claim 21, further comprising a window in the chamber.
- 26.(new) The injector of Claim 21, wherein the sidewalls, endwalls and cover plate are made of a polyvinylidene fluoride (PVDF) material.
- 27.(new) The injector of Claim 22, wherein the cover plate includes a flange extending laterally beyond the sidewalls and the endwalls, the flange being configured to support the etch injector when it is installed in the muffle.
- 28.(new) A method for removing residue from an apparatus configured to receive a gas injector assembly, the method comprising replacing the gas injector assembly with an etch chamber and introducing a liquid etchant into the etch chamber.

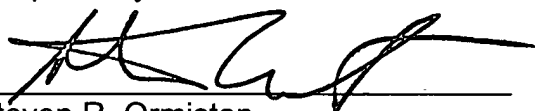
29.(new) A method for removing residue from an apparatus to receive a gas injector assembly for processing semiconductor wafers, the method comprising:  
replacing the gas injector assembly with an etch chamber; and  
introducing a liquid etchant into the etch chamber and on to a lower surface of the apparatus.

30.(new) The method of Claim 29, further comprising confining the liquid etchant to the etch chamber.

31.(new) The method of Claim 30, further comprising removing etchant vapors from the etch chamber.

32.(new) A method for removing residue from an apparatus configured to receive a gas injector assembly for processing semiconductor wafers, the method comprising:  
defining a deposition chamber in the apparatus;  
replacing the gas injector assembly with an etch chamber substantially co-extensive with the deposition chamber; and  
introducing a liquid etchant into the etch chamber and on to a lower surface of the apparatus.

Respectfully submitted,



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